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Defect-mediated polarization switching in ferroelectric films for low-power-consuming and ultra-high-density memories

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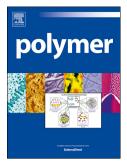
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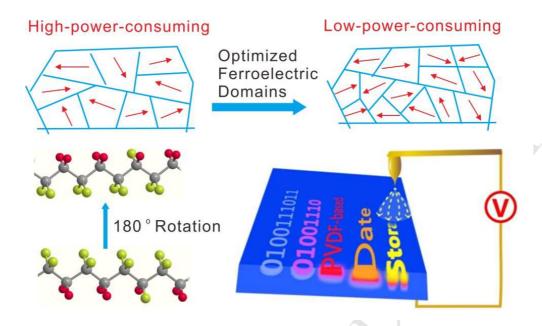
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Low-power-consuming, fast switching rate, and high usage temperature were attained in the defect-mediated P(VDF-TrFE) ultrathin films by using PFM testing. The excellent features in PVDF-based polymers can be potentially applied to many consumer electronics products, such as U-disk, CD-ROM, and digital versatile disks (DVD).

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